TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIII)

SSM6K24FE

High Speed Switching Applications

· Optimum for high-density mounting in small packages

• Low on-resistance: $R_{on} = 145m\Omega \text{ (max) } (@V_{GS} = 4.5 \text{ V})$

 $R_{on} = 180 m\Omega \text{ (max) (@V_{GS} = 2.5 V)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		V_{DS}	30	V	
Gate-Source voltage		V _{GSS}	± 12	V	
Drain current	DC	I _D	0.5	А	
	Pulse	I _{DP}	1.5		
Drain power dissipation		P _D (Note 1)	500	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

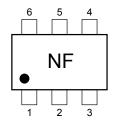
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the

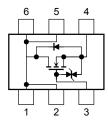
Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on FR4 board. (25.4 mm \times 25.4 mm \times 1.6 t, Cu Pad: 645 mm 2)

Marking



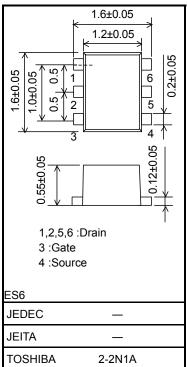
Equivalent Circuit (top view)



Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Unit: mm



Weight: 3.0 mg (typ.)



Electrical Characteristics (Ta = 25°C)

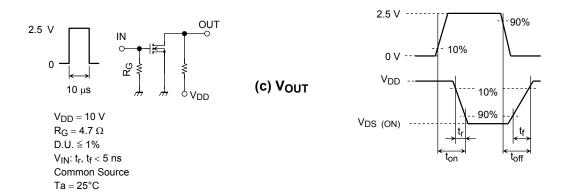
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0$	_	_	±1	μΑ	
Drain-Source breakdown voltage		V (BR) DSS	$I_D = 1 \text{ mA}, V_{GS} = 0$	30	_	_	- V	
		V (BR) DSX	$I_D = 1 \text{ mA}, V_{GS} = -12 \text{ V}$	18	_	_		
Drain cut-off curre	ent	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0	_	_	1	μА	
Gate threshold vo	oltage	V _{th}	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	0.5	_	1.1	V	
Forward transfer	admittance	Y _{fs}	$V_{DS} = 3 \text{ V}, I_D = 0.25 \text{ A}$ (Note2)	1.0	2.0	_	S	
Drain-Source on-resistance		R _{DS (ON)}	$I_D = 0.50 \text{ A}, V_{GS} = 4.5 \text{ V}$ (Note2)	_	120	145	- mΩ	
			I _D = 0.25 A, V _{GS} = 2.5 V (Note2)	_	140	180		
Input capacitance	;	C_{iss} $V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		_	245	_	pF	
Reverse transfer	capacitance	C _{rss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz		33	_	pF	
Output capacitance		C _{oss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz	_	41	_	pF	
Switching time	Turn-on time	t _{on}	V _{DD} = 10 V, I _D = 0.25 A,	_	9	_	ns	
	Turn-off time	t _{off}	$V_{GS} = 0~2.5 \text{ V}, R_G = 4.7 \Omega$	_	15	_		

Note2: Pulse test

Switching Time Test Circuit

(a) Test Circuit

(b) V_{IN}

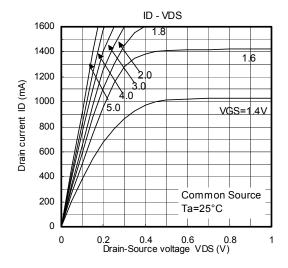


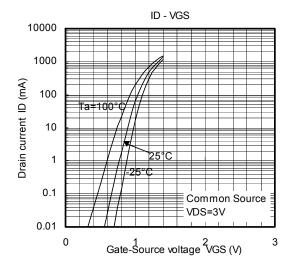
Precaution

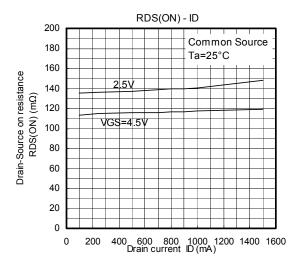
 V_{th} can be expressed as the voltage between gate and source when the low operating current value is I_D = 100 μ A for this product. For normal switching operation, $V_{GS~(on)}$ requires a higher voltage than V_{th} and $V_{GS~(off)}$ requires a lower voltage than V_{th} .

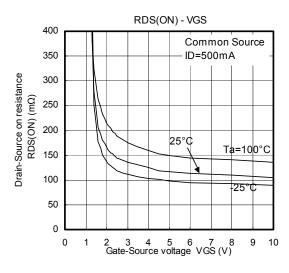
(The relationship can be established as follows: $V_{GS\ (off)}$ < V_{th} < $V_{GS\ (on)}$)

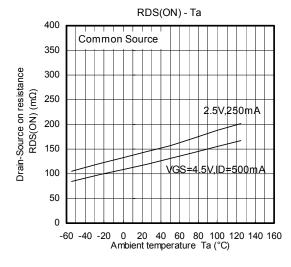
Please take this into consideration when using the device.

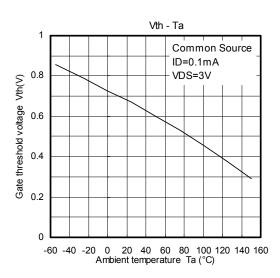




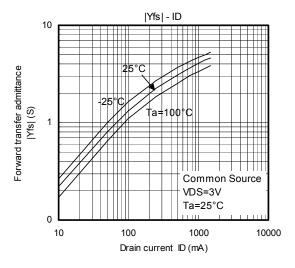


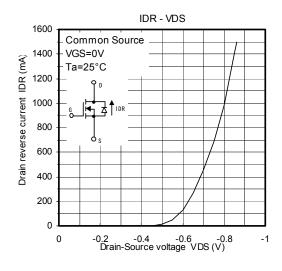


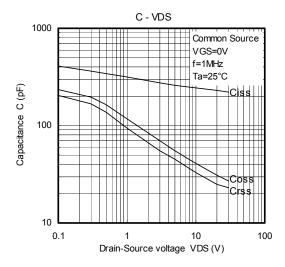


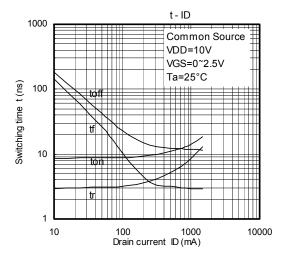


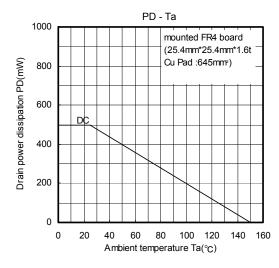
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20070701-EN GENERAL

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